

N-channel 30 V 1.0 m Ω logic level MOSFET in D2PAK 2 April 2014

Product data sheet

1. **General description**

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

Features and benefits 2.

- High efficiency due to low switching and conduction losses •
- Suitable for logic level gate drive sources

Applications 3.

- DC-to-DC converters •
- Load switiching
- Motor control
- Server power supplies

Quick reference data 4.

uick reference data						
Parameter	Conditions		Min	Тур	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	-	120	А
total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	306	W
junction temperature			-55	-	175	°C
cteristics	1				_	
drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12		-	0.89	1	mΩ
	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 13; Fig. 12		-	1.19	1.5	mΩ
aracteristics	·	·				
gate-drain charge	V_{GS} = 4.5 V; I _D = 75 A; V _{DS} = 15 V;		-	37	-	nC
total gate charge	<u>Fig. 14; Fig. 15</u>		-	118	-	nC
	Parameter drain-source voltage drain current total power dissipation junction temperature cteristics drain-source on-state resistance gate-drain charge	ParameterConditionsdrain-source voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ drain current $T_{mb} = 25 \ ^{\circ}C; V_{GS} = 10 \ V; Fig. 2$ total power dissipation $T_{mb} = 25 \ ^{\circ}C; Fig. 1$ junction temperature $T_{mb} = 25 \ ^{\circ}C; Fig. 1$ cteristicsdrain-source on-state resistance $V_{GS} = 10 \ V; \ I_D = 25 \ A; \ T_j = 25 \ ^{\circ}C; Fig. 12$ $V_{GS} = 10 \ V; \ I_D = 25 \ A; \ T_j = 100 \ ^{\circ}C; Fig. 13; Fig. 12$ aracteristicsgate-drain charge $V_{GS} = 4.5 \ V; \ I_D = 75 \ A; \ V_{DS} = 15 \ V; Fig. 14; Fig. 15$	ParameterConditionsdrain-source voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ drain current $T_{mb} = 25 \ ^{\circ}C; V_{GS} = 10 \ V; Fig. 2$ total power dissipation $T_{mb} = 25 \ ^{\circ}C; Fig. 1$ junction temperature $T_{mb} = 25 \ ^{\circ}C; Fig. 1$ cteristicsdrain-source on-state resistance $V_{GS} = 10 \ V; I_D = 25 \ A; T_j = 25 \ ^{\circ}C;$ Fig. 12 $V_{GS} = 10 \ V; I_D = 25 \ A; T_j = 100 \ ^{\circ}C;$ Fig. 13; Fig. 12aracteristicsgate-drain charge $V_{GS} = 4.5 \ V; I_D = 75 \ A; V_{DS} = 15 \ V;$ 	ParameterConditionsMindrain-source voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ -drain current $T_{mb} = 25 \ ^{\circ}C; V_{GS} = 10 \ V; Fig. 2$ [1]total power dissipation $T_{mb} = 25 \ ^{\circ}C; Fig. 1$ -junction temperature-55cteristicsdrain-source on-state resistance $V_{GS} = 10 \ V; \ I_D = 25 \ A; \ T_j = 25 \ ^{\circ}C; Fig. 12$ $V_{GS} = 10 \ V; \ I_D = 25 \ A; \ T_j = 100 \ ^{\circ}C; Fig. 12; V_{GS} = 10 \ V; \ I_D = 25 \ A; \ T_j = 100 \ ^{\circ}C; Fig. 13; Fig. 12-aracteristicsgate-drain chargeV_{GS} = 4.5 \ V; \ I_D = 75 \ A; \ V_{DS} = 15 \ V; I_D = 75 \ A; \ V_{S} = 15 \ V; I_D = 75 \ A; \ V_{S} = 15 \ V; I_D = 75 \ A; \ V_{S} = 15 \ V; I_D = 75 \ A; \ V_{S} = 15 \ V; I_D = 75 \ A; \ V_{S} = 15 \ V; I_D = 75 \ A; \ V_{S} = 15 \ V; I_D = 75 \ A; \ V_{S} = 15 \ V; I_D = 75 \ A; \ V_{S} = 15 \ V; I_D = 15 \$	ParameterConditionsMinTypdrain-source voltage $T_j \ge 25 ^\circ\text{C}; T_j \le 175 ^\circ\text{C}$ drain current $T_{mb} = 25 ^\circ\text{C}; V_{GS} = 10 \text{V}; \text{ Fig. 2}$ [1]-total power dissipation $T_{mb} = 25 ^\circ\text{C}; \text{ Fig. 1}$ junction temperature-55-drain-source on-state resistance $V_{GS} = 10 \text{V}; I_D = 25 \text{A}; T_j = 25 ^\circ\text{C};$ Fig. 12-0.89 $V_{GS} = 10 \text{V}; I_D = 25 \text{A}; T_j = 100 ^\circ\text{C};$ Fig. 13; Fig. 12-1.19aracteristicsgate-drain charge $V_{GS} = 4.5 \text{V}; I_D = 75 \text{A}; V_{DS} = 15 \text{V};$ -37	ParameterConditionsMinTypMaxdrain-source voltage $T_j \ge 25 ^\circ\text{C}; T_j \le 175 ^\circ\text{C}$ 30drain current $T_{mb} = 25 ^\circ\text{C}; V_{GS} = 10 \text{V}; Fig. 2$ [1]120total power dissipation $T_{mb} = 25 ^\circ\text{C}; Fig. 1$ 306junction temperature-55-175cteristicsdrain-source on-state resistance $V_{GS} = 10 \text{V}; I_D = 25 \text{A}; T_j = 25 ^\circ\text{C};$ Fig. 12-0.891V_{GS} = 10 V; I_D = 25 \text{A}; T_j = 100 ^\circ\text{C}; Fig. 13; Fig. 12-1.191.5aracteristicsgate-drain charge $V_{GS} = 4.5 \text{V}; I_D = 75 \text{A}; V_{DS} = 15 \text{V};$ -37-

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω; unclamped		-	-	1.9	J

[1] Continuous current is limited by package.

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain[1]		
3	S	source		G-UFA
mb	D	mounting base; connected to drain		mbb076 S
			D2PAK (SOT404)	

[1] It is not possible to make connection to pin 2

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMNR90-30BL	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMNR90-30BL	PSMNR90-30BL

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
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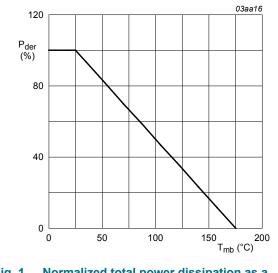
Product data sheet

PSMNR90-30BL

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Symbol	Parameter	Conditions		Min	Max	Unit
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	306	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	120	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	1573	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drai	n diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	1573	А
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 120 A; V _{sup} ≤ 30 V; R _{GS} = 50 Ω; unclamped		-	1.9	J

[1] Continuous current is limited by package.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

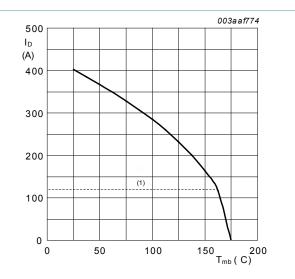
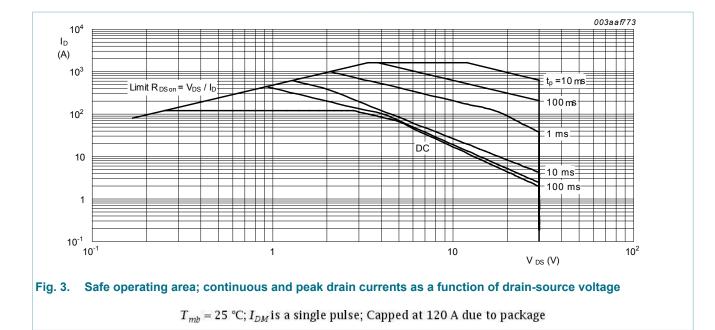


Fig. 2. Continuous drain current as a function of mounting base temperature.

 $V_{GS} \ge 10 \text{ V}; \quad (1) \text{ Capped at } 120 \text{ A due to package}$

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9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 4</u>		-	0.22	0.49	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board		-	50	-	K/W

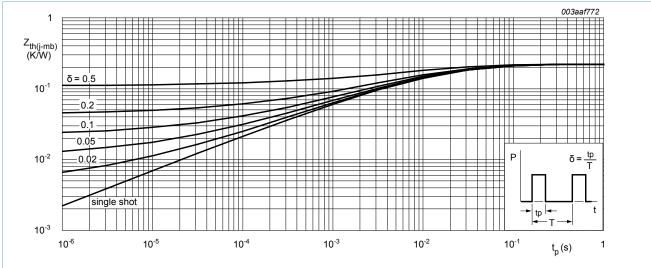


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

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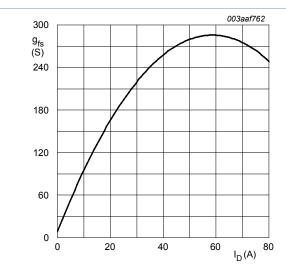
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	1.3	1.7	2.2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 11	0.65	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 11	-	-	2.5	V
I _{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	10	μA
		V_{DS} = 30 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	-	0.89	1	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 12	-	1.1	1.4	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 13; Fig. 12	-	1.65	2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 13; Fig. 12	-	1.19	1.5	mΩ
R _G	gate resistance	f = 1 MHz	-	1.1	-	Ω
Dynamic ch	aracteristics	· · · · ·				
Q _{G(tot)}	total gate charge	I _D = 75 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 14; Fig. 15	-	243	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	222	-	nC
		I _D = 75 A; V _{DS} = 15 V; V _{GS} = 4.5 V;	-	118	-	nC
Q _{GS}	gate-source charge	Fig. 14; Fig. 15	-	39	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	22	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	17	-	nC
Q _{GD}	gate-drain charge		-	37	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 75 A; V _{DS} = 15 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	2.8	-	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	V_{DS} = 15 V; V_{GS} = 0 V; f = 1 MHz;	-	14850	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	 -	2799	-	pF
C _{rss}	reverse transfer capacitance		-	1215	-	pF
t _{d(on)}	turn-on delay time	$\begin{split} V_{DS} &= 15 \text{ V}; \text{R}_{\text{L}} = 0.2 \Omega; \text{V}_{\text{GS}} = 5 \text{V}; \\ \text{R}_{\text{G}(\text{ext})} &= 5 \Omega; \text{I}_{\text{D}} = 75 \text{A}; \text{T}_{\text{j}} = 25 ^{\circ}\text{C} \end{split}$	-	95	-	ns
t _r	rise time	$\begin{split} V_{DS} &= 15 \text{ V}; \text{ R}_{L} = 0.2 \Omega; V_{GS} = 5 V; \\ \text{ R}_{G(ext)} &= 5 \Omega; T_{j} = 25 ^{\circ}\text{C}; I_{D} = 75 A \end{split}$	-	213	-	ns
t _{d(off)}	turn-off delay time	V_{DS} = 15 V; R_L = 0.2 Ω; V_{GS} = 5 V;	-	199	-	ns
t _f	fall time	$R_{G(ext)} = 5 \Omega; I_D = 75 A; T_j = 25 °C$	 -	115	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	I_{S} = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; V _{DS} = 15 V	-	67	-	ns
Qr	recovered charge		-	123	-	nC





 $T_j = 25 \,^\circ C; V_{DS} = 15 V$

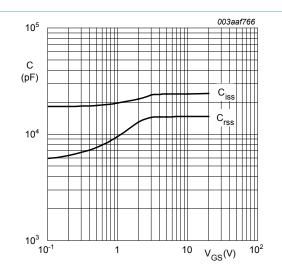
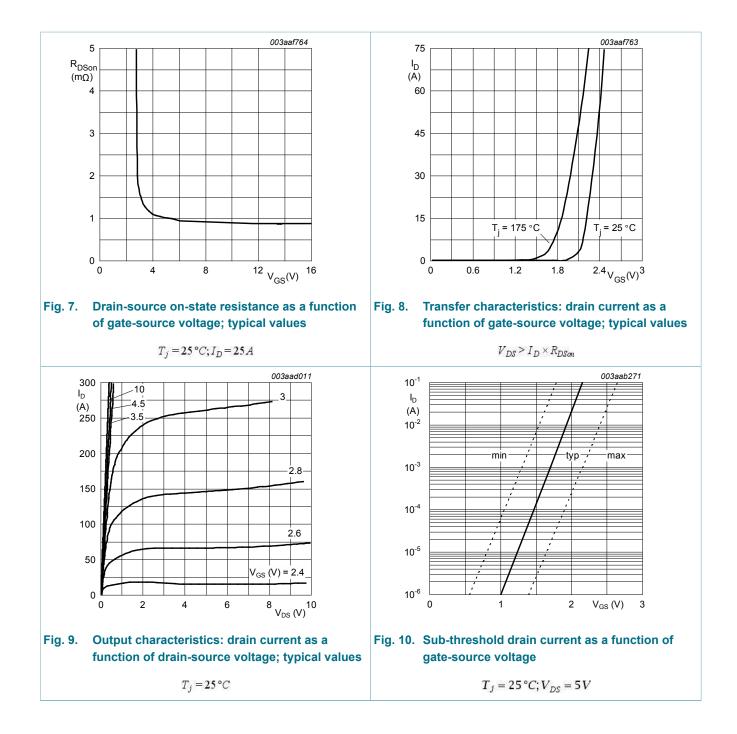


Fig. 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

 $V_{DS} = 0V; f = 1MHz$

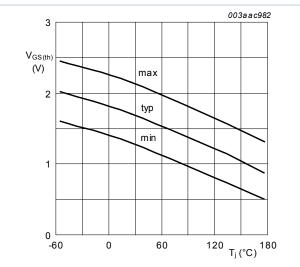
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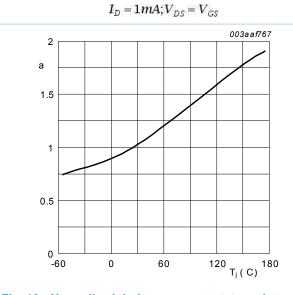


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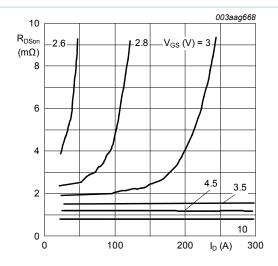








 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$





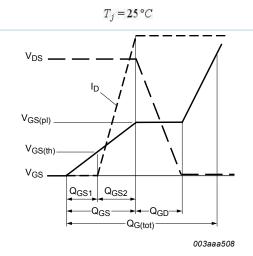
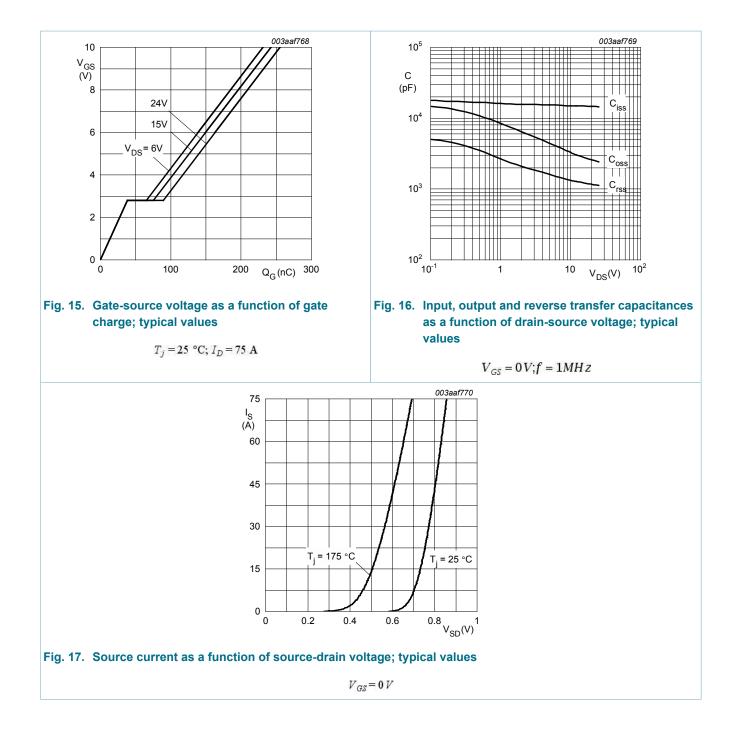


Fig. 14. Gate charge waveform definitions

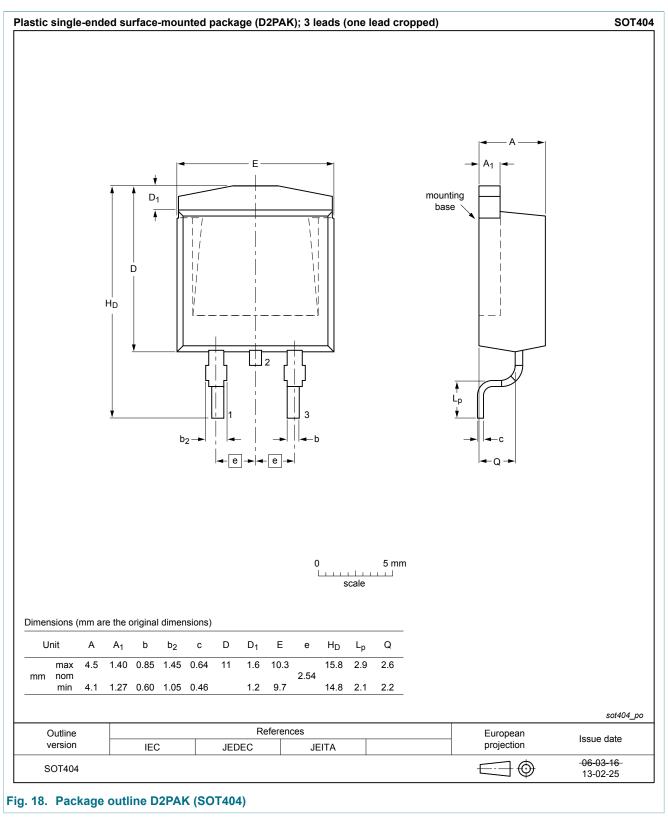
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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